

### KSC1674

# TV PIF Amplifier, FM Tuner RF Amplifier, Mixer, Oscillator

- High Current Gain Bandwidth Product : f<sub>T</sub>=600MHz (TYP.)
- High Power Gain : G<sub>PE</sub>=22dB at f=100MHz
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



1. Emitter 2. Base 3. Collector

### **NPN Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	20	V
V <sub>EBO</sub>	Emitter-Base Voltage	4	V
I <sub>C</sub>	Collector Current	20	mA
P <sub>C</sub>	Collector Power Dissipation	250	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

#### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =10μA, I <sub>E</sub> =0	30			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C=5$ mA, $I_B=0$	20			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	4			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =30V, $I_E$ =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =4V, $I_{C}$ =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	40		240	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA		0.72		V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.1	0.3	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	400	600		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =6V, I <sub>E</sub> =0, f=1MHz		1.2		pF
C <sub>c·rbb</sub> ,	Collector-Base Time Constant	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA f=31.9MHz		12	15	ps
NF	Noise Figure	$V_{CE}$ =6V, $I_{C}$ =1mA $R_{S}$ =50 $\Omega$ , f=100MHz		3.0	5.0	dB
G <sub>PE</sub>	Power Gain	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA, f=100MHz	18	22		dB

## **h**<sub>FE</sub> Classification

Classification	R	0	Υ
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120~ 240

## **Typical Characteristics**

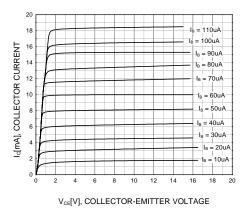
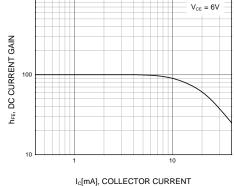


Figure 1. Static Characteristic



1000

Figure 2. DC current Gain

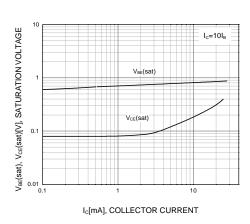


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

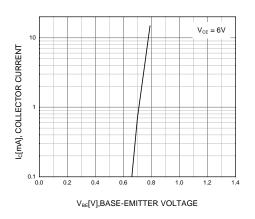


Figure 4. Base-Emitter On Voltage

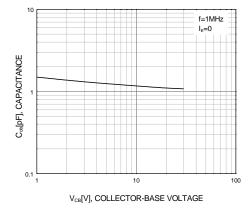


Figure 5. Collector Output Capacitance

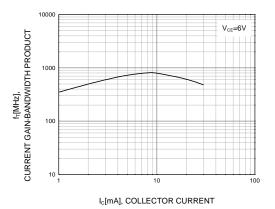
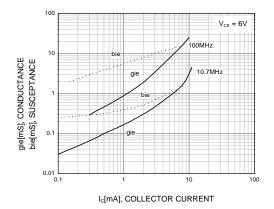


Figure 6. Current Gain Bandwidth Product

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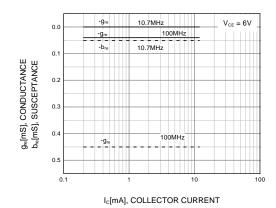
## **Typical Characteristics** (Continued)



1000 V<sub>CE</sub> = 6V V<sub>CE</sub>

Figure 7. Input Admittance (yie) vs. Collector Current

Figure 8. Forward Transfer Admittance (yfe) vs.
Collector Current



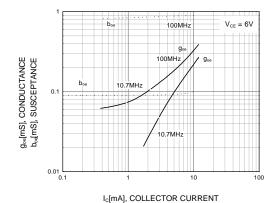
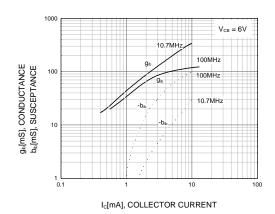


Figure 9. Reverse Transfer Admittance (yre) vs.
Collector Current

Figure 10. Output Admittance (yoe) vs. Collector Current



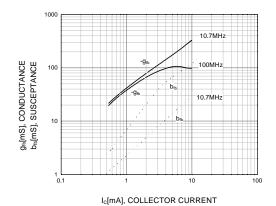


Figure 11. Input Admittance (yib) vs. Collector Current

Figure 12. Forward Transfer Admittance (yfb) vs.
Collector Current

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## Typical Characteristics (Continued)

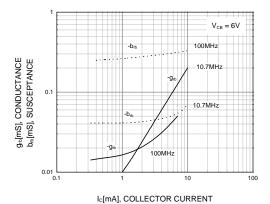


Figure 13. Reverse Transfer Admittance (yrb) vs.
Collector Current

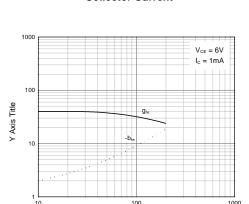


Figure 15. Forward Transfer Admittance (yfe) vs. Frequency

X axis title

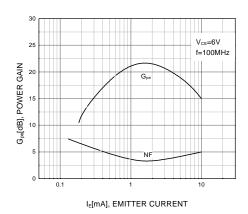


Figure 17. Power Gain and Noise Figure vs. Emitter Current

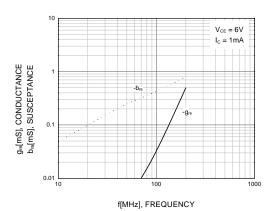


Figure 14. Reverse Transfer Admittance (yre) vs. Frequency

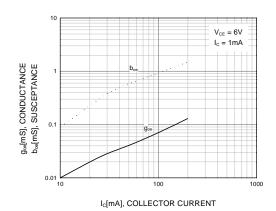


Figure 16. Output Admittance (yoe) vs. Frequency

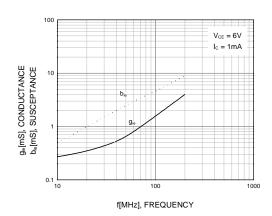
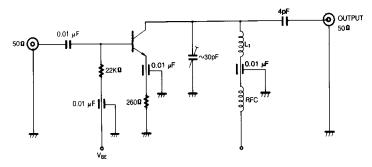


Figure 18. Input Admittance (yie) vs. Frequency

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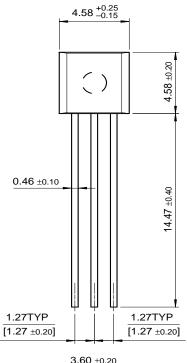
## Typical Characteristics (Continued)

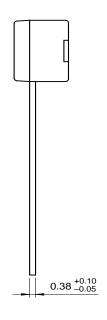
#### 100MHz Gpe, NF TEST CIRCUIT

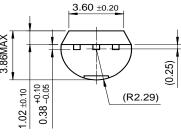


## **Package Demensions**

TO-92







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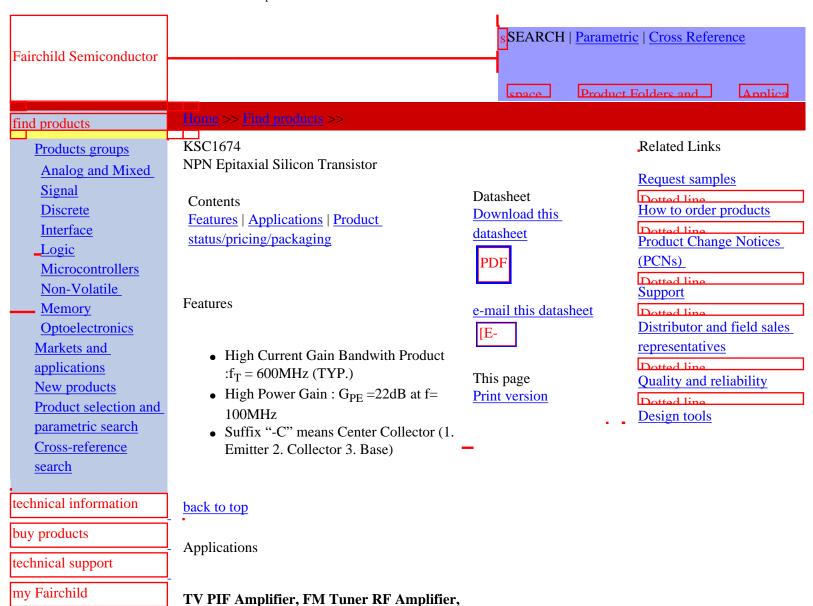
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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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company

Mixer, Oscillator

#### Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC1674COBU	Full Production	\$0.05	<u>TO-92</u>	3	BULK
KSC1674RTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL
KSC1674OBU	Full Production	\$0.05	<u>TO-92</u>	3	BULK
KSC1674RBU	Full Production	\$0.05	<u>TO-92</u>	3	BULK
KSC1674YBU	Full Production	\$0.05	<u>TO-92</u>	3	BULK
KSC1674CYTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL
KSC1674CYBU	Full Production	\$0.05	<u>TO-92</u>	3	BULK
KSC1674OTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL

Product Folder - Fairchild P/N KSC1674 - NPN Epitaxial Silicon Transistor

KSC1674COTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL
KSC1674YTA	Full Production	\$0.05	<u>TO-92</u>	3	TAPE REEL

<sup>\* 1,000</sup> piece Budgetary Pricing

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